
	<h2>SI7884BDP-T1-E3</h2>
	<p>Hersteller-Teilenummer: SI7884BDP-T1-E3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 40V 58A PPAK SO-8</p> <p>Datenblätter:  SI7884BDP-T1-E3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 104002 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI7884BDP-T1-E3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 40V 58A PPAK SO-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	104002 pcs Stock
detaillierte Beschreibung	N-Channel 40V 58A (Tc) 4.6W (Ta), 46W (Tc) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SO-8
Supplier Device-Gehäuse	PowerPAK® SO-8
Verlustleistung (max)	4.6W (Ta), 46W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	40V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	58A (Tc)
Rds On (Max) @ Id, Vgs	7.5 mOhm @ 16A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	77nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	3540pF @ 20V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI7884BDP-T1-E3-ND

SI7884BDP-T1-E3 ist neu im Original. Suche SI7884BDP-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7884BDP-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7884BDP-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI7884DP VISHAY VISHAY QFN</p>	 <p>SI7882DP-T1-E3 Vishay / Siliconix MOSFET N-CH 12V 13A PPAK SO-8</p>	 <p>SI7884BDP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 40V 58A PPAK SO-8</p>	 <p>SI7884BDP-T1-GE3 Vishay / Siliconix MOSFET N-CH 40V 58A PPAK SO-8</p>
 <p>SI7884BDP VISHAY SI7884BDP VISHAY</p>	 <p>SI7882DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 12V 13A PPAK SO-8</p>	 <p>SI7882DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 12V 13A PPAK SO-8</p>	 <p>SI7882DP-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 12V 13A PPAK SO-8</p>

heiße Teile

Mehr

SI7868ADP	SI7868ADP-T1-E3	SI7868ADP-T1-E3	SI7868ADP-T1-GE3	SI7868ADP-T1-GE3
SI7868DP-T1	SI7868DP-T1-E3	SI7868DP-T1-GE3	SI786LG-T1	SI786LG-T1-E3
SI7872DP	SI7872DP-T1-E3	SI7872DP-T1-E3	SI7872DP-T1-GE3	SI7872DP-T1-GE3
SI7880ADP-T1-E3	SI7880ADP-T1-E3	SI7880ADP-T1-GE3	SI7880ADP-T1-GE3	SI7880DP-T1-GE3
SI7882DP-T1-E3	SI7882DP-T1-E3	SI7882DP-T1-GE3	SI7882DP-T1-GE3	SI7884BDP
SI7884BDP-T1-E3	SI7884BDP-T1-GE3	SI7884BDP-T1-GE3	SI7884DP-T1-E3	SI7884DP-T1-GE3
SI7886ADP-T1-E3	SI7886ADP-T1-E3	SI7886ADP-T1-GE3	SI7886ADP-T1-GE3	SI7886DP
SI7886DP-T1	SI7886DP-T1-E3	SI7886DP-T1-GE3	SI7888DP-T1-E3	SI7888DP-T1-E3
SI7888DP-T1-GE3	SI7888DP-T1-GE3	SI7892ADP-T1-E3	SI7892ADP-T1-GE3	SI7892ADP-T1-GE3
SI7892BDP-T1-E3	SI7892BDP-T1-E3	SI7892BDP-T1-GE3	SI7892BDP-T1-GE3	SI7892DP

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